

APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

Title of Invention	High fT and fmax Bipolar Transistor and Method of Making Same	
Application Type: regular, utility Attorney Docket Number: BUR920030004US1		
Correspondence address: Customer Number: 021018 		
Inventors Information: <u>Inventor 1:</u> Applicant Authority Type: Inventor Citizenship: IN Given Name: Alvin Middle Name: Jose Family Name: Joseph City of Residence: Williston State of Residence: VT Country of Residence: US Address-1 of Mailing Address: 109 Coyote Lane Address-2 of Mailing Address: City of Mailing Address: Williston State of Mailing Address: VT Postal Code of Mailing Address: 05495 Country of Mailing Address: US Phone: Fax: E-mail: <u>Inventor 2:</u> Applicant Authority Type: Inventor		

Citizenship: CN
Given Name: Qizhi
Family Name: Liu
City of Residence: Essex Junction
State of Residence: VT
Country of Residence: US
Address-1 of Mailing Address: 124 Sandhill Road
Address-2 of Mailing Address: #3
City of Mailing Address: Essex Junction
State of Mailing Address: VT
Postal Code of Mailing Address: 05452
Country of Mailing Address: US
Phone:
Fax:
E-mail:

Attorney Information:

Name	Registration Number
Anthony J. Canale	51,526

Assignee 1:

Organization Name: International Business Machines Corporation
Address-1 of Mailing Address: New Orchard Road
Address-2 of Mailing Address:
City of Mailing Address: Armonk
State of Mailing Address: NY
Postal Code of Mailing Address:
Country of Mailing Address: US
Phone:
Fax:
E-mail: